

HiPerFRED

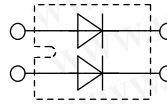
High Performance Fast Recovery Diode
Low Loss and Soft Recovery
Parallel legs

Part number

DSEP2x61-06A

勝特力材料 886-3-5753170
勝特力电子(上海) 86-21-34970699
勝特力电子(深圳) 86-755-83298787
[Http://www.100y.com.tw](http://www.100y.com.tw)

$V_{RRM} = 600\text{ V}$
 $I_{FAV} = 2 \times 60\text{ A}$
 $t_{rr} = 35\text{ ns}$



Backside: isolated

E72873

Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low I_{rm} -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{rm} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

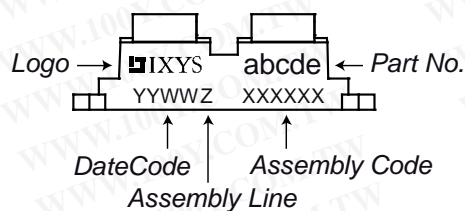
Package:

- Housing: SOT-227B (minibloc)
- Industry standard outline
- Cu base plate internal DCB isolated
- Isolation Voltage 3000 V
- Epoxy meets UL 94V-0
- RoHS compliant

Ratings

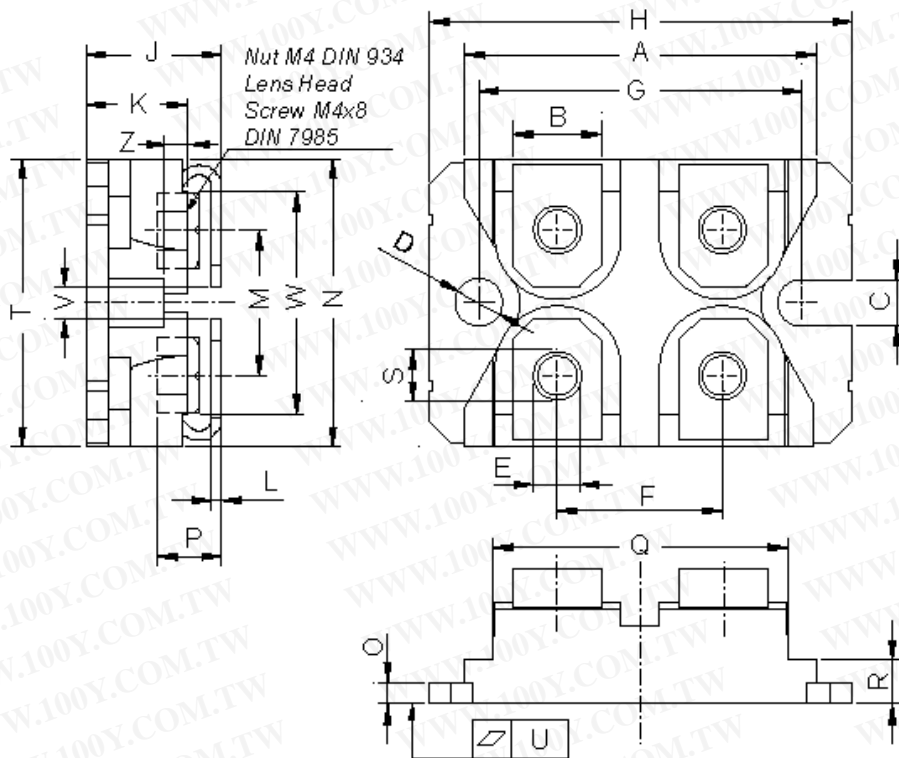
Symbol	Definition	Conditions	min.	typ.	max.	Unit
V_{RRM}	max. repetitive reverse voltage	$T_{VJ} = 25^{\circ}\text{C}$			600	V
I_R	reverse current	$V_R = 600\text{ V}$ $T_{VJ} = 25^{\circ}\text{C}$			650	μA
V_F	forward voltage	$V_R = 600\text{ V}$ $T_{VJ} = 150^{\circ}\text{C}$			2.5	mA
		$I_F = 60\text{ A}$ $T_{VJ} = 25^{\circ}\text{C}$			2.01	V
		$I_F = 120\text{ A}$ $T_{VJ} = 25^{\circ}\text{C}$			2.27	V
		$I_F = 60\text{ A}$ $T_{VJ} = 150^{\circ}\text{C}$			1.35	V
$I_F = 120\text{ A}$ $T_{VJ} = 150^{\circ}\text{C}$			1.63	V		
I_{FAV}	average forward current	rectangular $d = 0.5$ $T_C = 65^{\circ}\text{C}$			60	A
V_{F0}	threshold voltage	$T_{VJ} = 150^{\circ}\text{C}$			1.09	V
r_F	slope resistance				4.3	m Ω
R_{thJC}	thermal resistance junction to case				0.85	K/W
T_{VJ}	virtual junction temperature		-40		150	$^{\circ}\text{C}$
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$			140	W
I_{FSM}	max. forward surge current	$t = 10\text{ ms}$ (50 Hz), sine $T_{VJ} = 45^{\circ}\text{C}$			600	A
I_{RM}	max. reverse recovery current	$T_{VJ} = 25^{\circ}\text{C}$			18	A
		$I_F = 60\text{ A}; V_R = 300\text{ V}$ $T_{VJ} = 100^{\circ}\text{C}$			30	A
t_{rr}	reverse recovery time	$-di_F/dt = 600\text{ A}/\mu\text{s}$ $T_{VJ} = 25^{\circ}\text{C}$			30	ns
		$T_{VJ} = 100^{\circ}\text{C}$			55	ns
C_J	junction capacitance	$V_R = 400\text{ V}; f = 1\text{ MHz}$ $T_{VJ} = 25^{\circ}\text{C}$			67	pF

Symbol	Definition	Conditions	Ratings			Unit
			min.	typ.	max.	
I_{RMS}	RMS current	per terminal			100	A
R_{thCH}	thermal resistance case to heatsink			0.10		K/W
T_{stg}	storage temperature		-40		150	°C
Weight				30		g
M_D	mounting torque		1.1		1.5	Nm
M_T	terminal torque		1.1		1.5	Nm
V_{ISOL}	isolation voltage	t = 1 second	3000			V
		t = 1 minute	2500			V
$d_{Spp/App}$	creepage striking distance on surface through air	terminal to terminal	10.5	3.2		mm
$d_{Spb/Abp}$	creepage striking distance on surface through air	terminal to backside	8.6	6.8		mm

Product Marking


Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Code Key
Standard	DSEP2x61-06A	DSEP2x61-06A	Tube	10	474754

Outlines SOT-227B (minibloc)



Dim.	Millimeter		Inches	
	min	max	min	max
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	37.80	38.23	1.488	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.74	0.84	0.029	0.033
M	12.50	13.10	0.492	0.516
N	25.15	25.42	0.990	1.001
O	1.95	2.13	0.077	0.084
P	4.95	6.20	0.195	0.244
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.167
S	4.55	4.85	0.179	0.191
T	24.59	25.25	0.968	0.994
U	-0.05	0.10	-0.002	0.004
V	3.20	5.50	0.126	0.217
W	19.81	21.08	0.780	0.830
Z	2.50	2.70	0.098	0.106

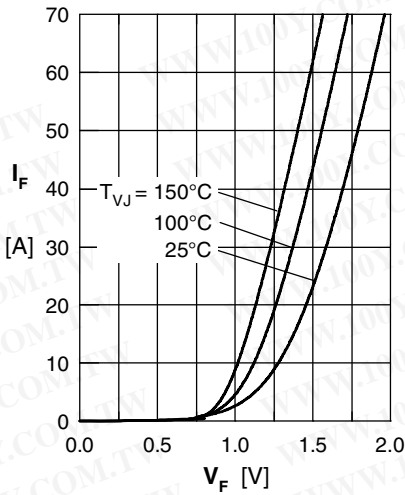


Fig. 1 Forward current I_F vs. V_F

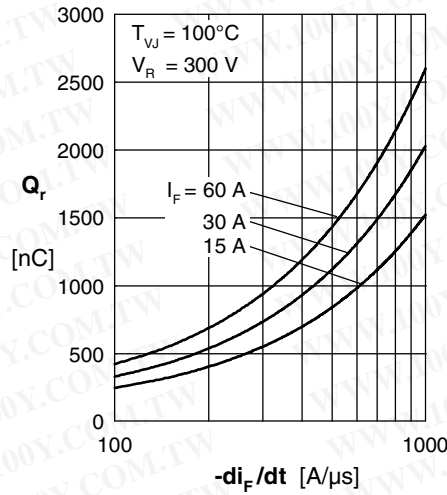


Fig. 2 Reverse recovery charge Q_r versus $-di_F/dt$

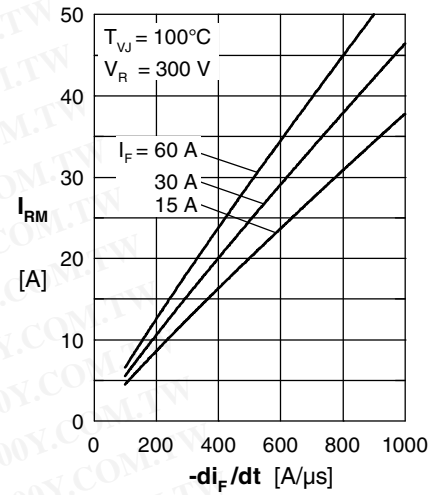


Fig. 3 Peak reverse current I_{RM} versus $-di_F/dt$

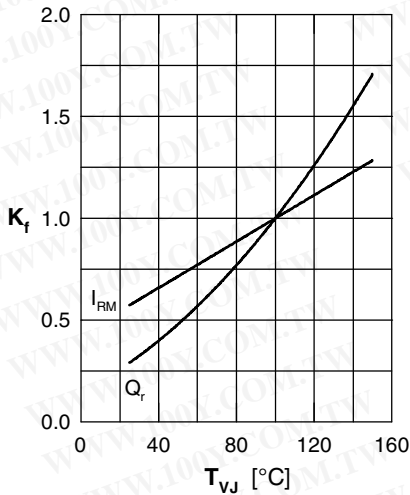


Fig. 4 Dynamic parameters Q_r , I_{RM} versus T_{VJ}

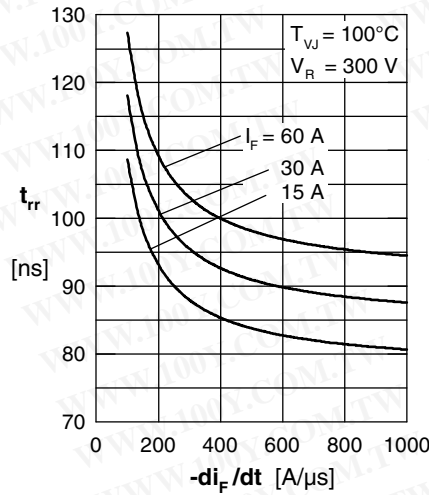


Fig. 5 Recovery time t_{rr} versus $-di_F/dt$

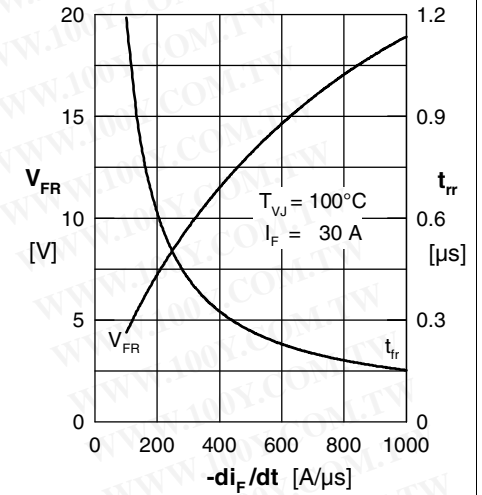


Fig. 6 Peak forward voltage V_{FR} and t_{fr} versus di_F/dt

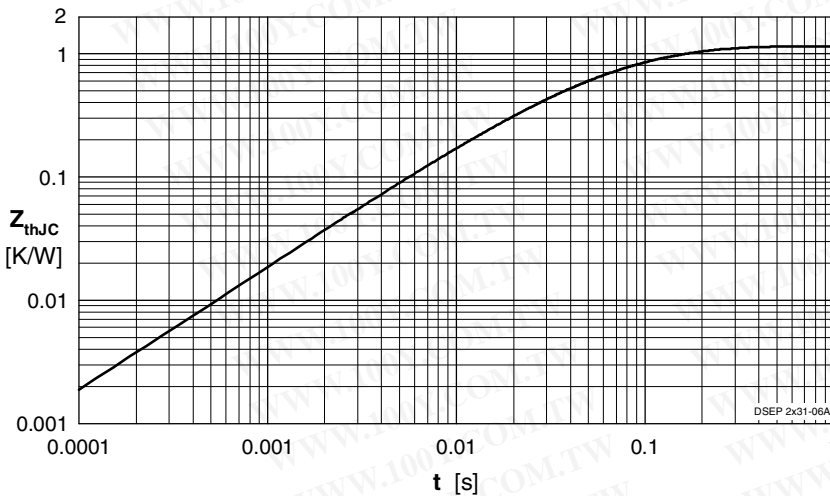


Fig. 7 Transient thermal resistance junction to case

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.436	0.0055
2	0.482	0.0092
3	0.117	0.0007
4	0.115	0.0418